INTEGRATED CIRCUITS

DATA SHEET



74LVT103.3V Triple 3-input NAND gate

Product specification

1996 May 29

IC24 Data Handbook





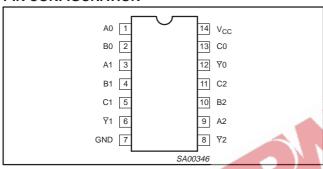
3.3V Triple 3-input NAND gate

74LVT10

QUICK REFERENCE DATA

| SYMBOL | PARAMETER | CONDITIONS T _{amb} = 25°C; GND = 0V | TYPICAL | UNIT |
|--------------------------------------|---|--|------------|------|
| [†] PLH [†] PHL | Propagation delay An, Bn, Cn to Yn | $C_L = 50pF;$ $V_{CC} = 3.3V$ | 3.8 3.3 | ns |
| C _{IN} | Input capacitance | V _I = 0V or 3.0V | 2 | pF |
| I _{CCL} | Total supply current | Outputs Low; V _{CC} = 3.6V | 1 | mA |

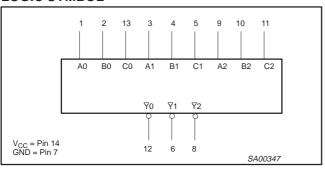
PIN CONFIGURATION



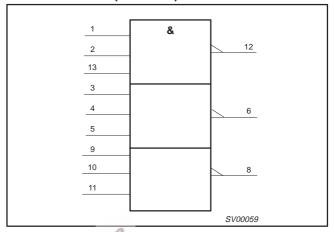
PIN DESCRIPTION

| | _ | |
|---------------------------------|-----------------|-------------------------|
| PIN NUMBER | SYMBOL | NAME AND FUNCTION |
| 1, 2, 3, 4, 5, 9, 10, 11, 13 | An, Bn, Cn | Data inputs |
| 6, 8, 12 | ₹n | Data outputs |
| 7 | GND | Ground (0V) |
| 14 | V _{CC} | Positive supply voltage |

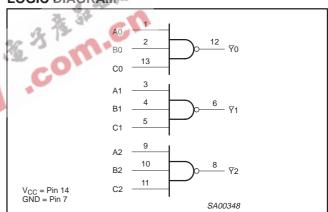
LOGIC SYMBOL



LOGIC SYMBOL (IEEE/IEC)



LOGIC DIAGRAM



FUNCTION TABLE

| | INPUTS | | OUTPUTS |
|-----|--------|-----|---------|
| Dna | Dnb | Dnc | Qn |
| L | L | L | Н |
| L | L | Н | Н |
| L | Н | L | Н |
| L | Н | Н | Н |
| н | L | L | Н |
| Н | L | Н | Н |
| н | Н | L | Н |
| Н | Н | Н | L |

NOTES:

H = High voltage level
L = Low voltage level

ORDERING INFORMATION

| PACKAGES | TEMPERATURE RANGE | OUTSIDE NORTH AMERICA | NORTH AMERICA | DWG NUMBER |
|----------------------|-------------------|-----------------------|---------------|------------|
| 14-Pin Plastic SO | -40°C to +85°C | 74LVT10 D | 74LVT10 D | SOT108-1 |
| 14-Pin Plastic SSOP | -40°C to +85°C | 74LVT10 DB | 74LVT10 DB | SOT337-1 |
| 14-Pin Plastic TSSOP | -40°C to +85°C | 74LVT10 PW | 74LVT10PW DH | SOT402-1 |

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ABSOLUTE MAXIMUM RATINGS1, 2

| SYMBOL | PARAMETER | CONDITIONS | RATING | UNIT |
|------------------|--------------------------------|-----------------------------|--------------|------|
| V _{CC} | DC supply voltage | | -0.5 to +4.6 | V |
| I _{IK} | DC input diode current | V _I < 0 | -50 | mA |
| VI | DC input voltage ³ | | -0.5 to +7.0 | V |
| I _{OK} | DC output diode current | V _O < 0 | -50 | mA |
| V _{OUT} | DC output voltage ³ | Output in Off or High state | -0.5 to +7.0 | V |
| | DC output ourront | Output in High state | -32 | mA |
| lout | DC output current | Output in Low state | 64 | IIIA |
| T _{stg} | Storage temperature range | | -65 to 150 | °C |

NOTES:

RECOMMENDED OPERATING CONDITIONS

| CVMDOL | PARAMETER | LIM | ITS | UNIT |
|------------------|---|-----|-----|------|
| SYMBOL | PARAMETER | MIN | MAX | UNII |
| V _{CC} | DC supply voltage | 2.7 | 3.6 | V |
| VI | Input voltage | 0 | 5.5 | V |
| V_{IH} | High-level input voltage | 2.0 | | V |
| V_{IL} | Low-level Input voltage | | 0.8 | V |
| I _{OH} | High-level output current | | -20 | mA |
| I _{OL} | Low-level output current | | 32 | mA |
| Δt/Δν | Input transition rise or fall rate; Outputs enabled | | 10 | ns/V |
| T _{amb} | Operating free-air temperature range | -40 | +85 | °C |

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Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
 The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.
 The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

3.3V Triple 3-input NAND gate

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DC ELECTRICAL CHARACTERISTICS

Over recommended operating conditions Voltages are referenced to GND (ground = 0V)

| | | | ı | IMITS | | | |
|------------------|--|---|------------------------|-----------------|-------|------|--|
| SYMBOL | PARAMETER | TEST CONDITIONS | Temp = - | 40°C to | +85°C | UNIT | |
| | | | MIN TYP ¹ M | | MAX | λX | |
| V _{IK} | Input clamp voltage | V _{CC} = 2.7V; I _{IK} = -18mA | | | -1.2 | V | |
| | | $V_{CC} = 2.7 \text{ to } 3.6 \text{V}; I_{OH} = -100 \mu\text{A}$ | V _{CC} -0.2 | V _{CC} | | | |
| V_{OH} | High-level output voltage | V _{CC} = 2.7V; I _{OH} = -6mA | 2.4 | 2.5 | | V | |
| | | $V_{CC} = 3.0V; I_{OH} = -20mA$ | 2.0 | 2.3 | | | |
| | | $V_{CC} = 2.7V; I_{OL} = 100\mu A$ | | 0.05 | 0.2 | | |
| V_{OL} | Low-level output voltage | V _{CC} = 2.7V; I _{OL} = 24mA | | 0.3 | 0.5 | V | |
| | | V _{CC} = 3.0V; I _{OL} = 32mA | | 0.35 | 0.5 | | |
| | lanut lankaga aurrant | $V_{CC} = 0 \text{ or } 3.6V; V_I = 5.5V$ | | 0.1 | 10 | | |
| I _I | Input leakage current | $V_{CC} = 3.6V$; $V_I = V_{CC}$ or GND | | 0.01 | ±1 | μΑ | |
| I _{OFF} | Output off current | $V_{CC} = 0V; V_{I} \text{ or } V_{O} = 0 \text{ to } 4.5V$ | | 1 | ±100 | μΑ | |
| I _{CCH} | Quigocont gunphy gurrent | V_{CC} = 3.6V; Outputs High, V_{I} = GND or V_{CC} , I_{O} = 0 | | 0.001 | 0.02 | mA | |
| I _{CCL} | Quiescent supply current | V_{CC} = 3.6V; Outputs Low, V_1 = GND or V_{CC} , I_{O} = 0 | | 1 | 2 | | |
| Δl _{CC} | Additional supply current per input pin ² | V_{CC} = 3V to 3.6V; One input at V_{CC} –0.6V, Other inputs at V_{CC} or GND | | 0.1 | 0.2 | mA | |
| C _I | Input capacitance | $V_1 = 3V$ or 0 | | 2 | | pF | |

NOTES:

- All typical values are at V_{CC} = 3.3V and T_{amb} = 25°C.
 This is the increase in supply current for each input at the specificed voltage level other than V_{CC} or GND.

AC CHARACTERISTICS

GND = 0V; t_R = t_F = 2.5ns; C_L = 50pF, R_L = 500 Ω ; T_{amb} = -40°C to +85°C.

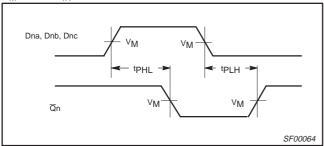
| SYMBOL | PARAMETER | WAVEFORM | V _C | $_{2}$ = 3.3V \pm 0 | .3V | V _{CC} = 2.7V | UNIT |
|--------------------------------------|---------------------------------------|----------|----------------|-----------------------|------------|------------------------|------|
| | | | MIN | TYP ¹ | MAX | MAX | |
| t _{PLH} t _{PHL} | Propagation delay An, Bn, Cn to ₹n | 1 | 1.0 1.0 | 3.8 3.3 | 5.2 4.4 | 6.2 4.4 | ns |

NOTE:

1. All typical values are at V_{CC} = 3.3V and T_{amb} = 25°C.

AC WAVEFORMS

 $V_M = 1.5V$, $V_{IN} = GND$ to 2.7V



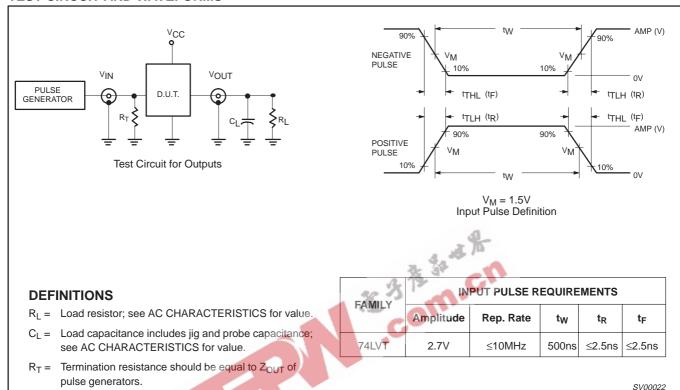
Waveform 1. Propagation Delay for Inverting Outputs

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TEST CIRCUIT AND WAVEFORMS



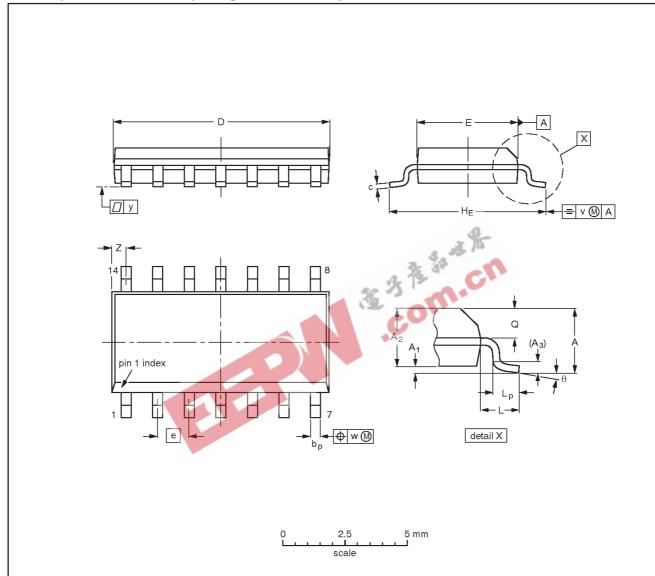
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SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

| UNIT | A max. | A ₁ | A ₂ | A ₃ | bp | С | D ⁽¹⁾ | E ⁽¹⁾ | е | HE | L | Lp | Q | v | w | у | Z ⁽¹⁾ | θ |
|--------|-----------|----------------|----------------|----------------|--------------|------------------|------------------|------------------|-------|----------------|-------|----------------|----------------|------|------|-------|------------------|----|
| mm | 1.75 | 0.25 0.10 | 1.45 1.25 | 0.25 | 0.49 0.36 | 0.25 0.19 | 8.75 8.55 | 4.0 3.8 | 1.27 | 6.2 5.8 | 1.05 | 1.0 0.4 | 0.7 0.6 | 0.25 | 0.25 | 0.1 | 0.7 0.3 | 8° |
| inches | 0.069 | 0.010 0.004 | 0.057 0.049 | 0.01 | | 0.0100 0.0075 | 0.35 0.34 | 0.16 0.15 | 0.050 | 0.244 0.228 | 0.041 | 0.039 0.016 | 0.028 0.024 | 0.01 | 0.01 | 0.004 | 0.028 0.012 | 0° |

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

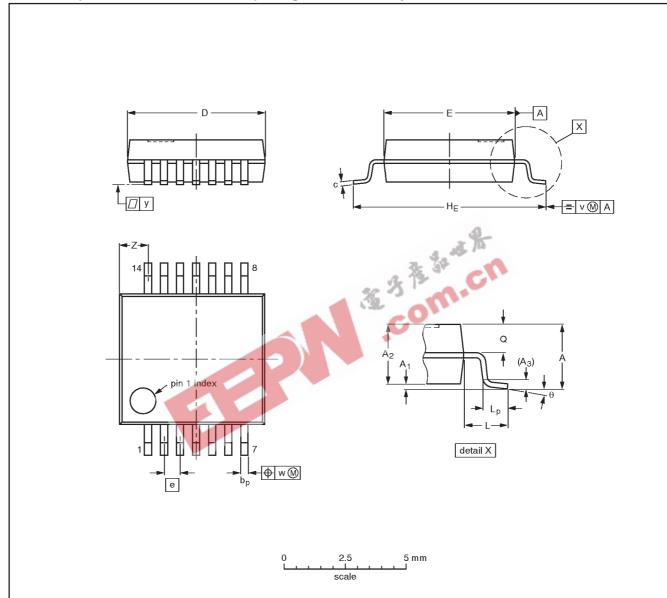
| OUTLINE | | REFER | EUROPEAN | ISSUE DATE | | | |
|----------|---------|----------|----------|------------|------------|---------------------------------|--|
| VERSION | IEC | JEDEC | EIAJ | | PROJECTION | ISSUE DATE | |
| SOT108-1 | 076E06S | MS-012AB | | | | 95-01-23 97-05-22 | |

3.3V Triple 3-input NAND gate

74LVT10

SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



DIMENSIONS (mm are the original dimensions)

| | | | | | | -, | | | | | | | | | | | | |
|------|-----------|----------------|----------------|----------------|--------------|--------------|------------------|------------------|------|------------|------|--------------|------------|-----|------|-----|------------------|----------|
| UNIT | A max. | Α ₁ | A ₂ | A ₃ | bp | С | D ⁽¹⁾ | E ⁽¹⁾ | е | HE | L | Lp | Q | v | w | у | Z ⁽¹⁾ | θ |
| mm | 2.0 | 0.21 0.05 | 1.80 1.65 | 0.25 | 0.38 0.25 | 0.20 0.09 | 6.4 6.0 | 5.4 5.2 | 0.65 | 7.9 7.6 | 1.25 | 1.03 0.63 | 0.9 0.7 | 0.2 | 0.13 | 0.1 | 1.4 0.9 | 8° 0° |

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

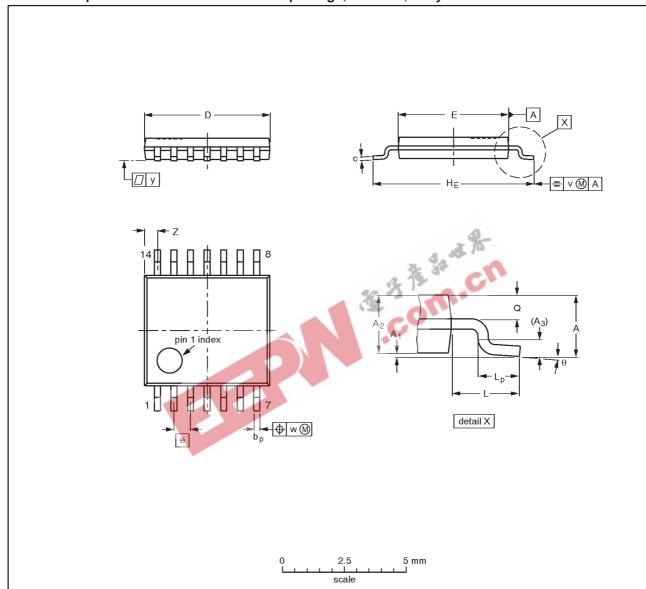
| OUTLINE | | REFER | EUROPEAN | ISSUE DATE | |
|----------|-----|----------|----------|------------|----------------------------------|
| VERSION | IEC | JEDEC | EIAJ | PROJECTION | ISSUEDATE |
| SOT337-1 | | MO-150AB | | | -95-02-04 96-01-18 |

3.3V Triple 3-input NAND gate

74LVT10

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



DIMENSIONS (mm are the original dimensions)

| UNIT | A max. | Α1 | A ₂ | Α3 | рb | c | D ⁽¹⁾ | E ⁽²⁾ | e | HE | ٦ | Lp | Ø | v | w | у | Z ⁽¹⁾ | θ |
|------|-----------|--------------|----------------|------|--------------|------------|------------------|------------------|------|------------|-----|--------------|------------|-----|------|-----|------------------|----------|
| mm | 1.10 | 0.15 0.05 | 0.95 0.80 | 0.25 | 0.30 0.19 | 0.2 0.1 | 5.1 4.9 | 4.5 4.3 | 0.65 | 6.6 6.2 | 1.0 | 0.75 0.50 | 0.4 0.3 | 0.2 | 0.13 | 0.1 | 0.72 0.38 | 8° 0° |

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

| OUTLINE VERSION | | REFER | EUROPEAN | ISSUE DATE | | |
|--------------------|-----|--------|----------|------------|------------|---------------------------------|
| | IEC | JEDEC | EIAJ | | PROJECTION | ISSUE DATE |
| SOT402-1 | | MO-153 | | | | 94-07-12 95-04-04 |

3.3V Triple 3-input NAND gate

74LVT10

NOTES



3.3V Triple input NAND gate

74LVT10



| DEFINITIONS | | | | | | |
|---------------------------|------------------------|--|--|--|--|--|
| Data Sheet Identification | Product Status | Definition | | | | |
| Objective Specification | Formative or in Design | This data sheet contains the design target or goal specifications for product development. Specifications may change in any manner without notice. | | | | |
| Preliminary Specification | Preproduction Product | This data sheet contains preliminary data, and supplementary data will be published at a later date. Philip Semiconductors reserves the right to make changes at any time without notice in order to improve desig and supply the best possible product. | | | | |
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